

Application No. 10/790,403

Filed: March 1, 2004

TC Art Unit: 2822

Confirmation No.: 1449

IN THE FIGURES

Please replace Figs. 1-32 with the replacement figures accompanying this amendment. Fig. 3 has been amended to substitute reference number -- 24 -- for reference number -- 22 --. No new matter has been added.

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REMARKS

Claims 1-31 are currently pending. Claims 1-12 and claims 27-31 have been withdrawn from prosecution. Claims 13-23 have been allowed. Claims 24-26 have been rejected under 35 U.S.C. § 102(e). Claim 24 has been amended. The Applicants respectfully request reconsideration of the pending application in view of the above amendment and for the following reasons. The Examiner is encouraged to telephone the undersigned attorney to discuss any matter that would expedite allowance of the present application.

35 U.S.C § 102(e) REJECTIONS

The Examiner has rejected claims 24-26 under 35 U.S.C. § 102(e) as anticipated by U.S. Patent Application Publication Number 2001/0032977 to Abe, et al. ("Abe"). The Applicants respectfully traverse these rejections in view of the amendment to claim 24 and for the following reasons.

Independent claim 24 currently recites that the method includes:

bonding a silicon surface of said second body to the silicon dioxide layer of the first body by heating the hydrogen implanted body to promote cleaving or fracturing of regions containing hydrogen from regions not containing hydrogen, wherein a first heating step to a cleaving temperature is followed by a second heating step to a bond strengthening temperature.

The Abe reference does not teach, mention or suggest such a feature. Abe teaches bonding a bond wafer to a base wafer at room temperature and annealing the wafers at a higher temperature.

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See, e.g., Abe, ¶¶ 0059, 0062, and 0063. However, Abe is silent about first heating the wafers to a cleaving temperature (about 600 degrees C) to promote cleavage of the hydrogen regions from the non-hydrogen regions and further heating the wafers to a higher, bond strengthening temperature (about 1000 degrees C).

Accordingly, the Applicants believe that claims 24-26 are not anticipated by the Abe reference and, further, satisfy all of the requirements of 35 U.S.C. §§ 101, et seq., especially § 102(e). As such, the claims are in condition for allowance.

The Examiner is encouraged to telephone the undersigned attorney to discuss any matter that would expedite allowance of the present application.

Respectfully submitted,

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